

## P-Channel 2.5 V (G-S) MOSFET

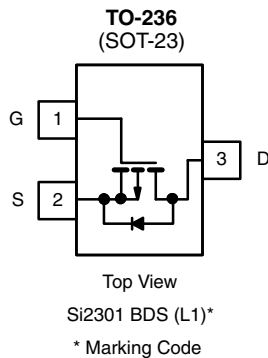
PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>b</sup>
- 20	0.100 at $V_{GS} = - 4.5$ V	- 2.4
	0.150 at $V_{GS} = - 2.5$ V	- 2.0

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS\***  
COMPLIANT  
HALOGEN  
**FREE**  
Available



Ordering Information: Si2301BDS-T1-E3 (Lead (Pb)-free)  
Si2301BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	- 20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>b</sup>	$I_D$	$T_A = 25$ °C	- 2.4	- 2.2	A
		$T_A = 70$ °C	- 1.9	- 1.8	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	- 10			
Continuous Source Current (Diode Conduction) <sup>b</sup>	$I_S$	- 0.72	- 0.6		
Power Dissipation <sup>b</sup>	$P_D$	$T_A = 25$ °C	0.9	0.7	W
		$T_A = 70$ °C	0.57	0.45	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	120	145	°C/W
Maximum Junction-to-Ambient <sup>c</sup>		140	175	

Notes:

- Pulse width limited by maximum junction temperature.
- Surface mounted on FR4 board,  $t \leq 5$  s.
- Surface mounted on FR4 board.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

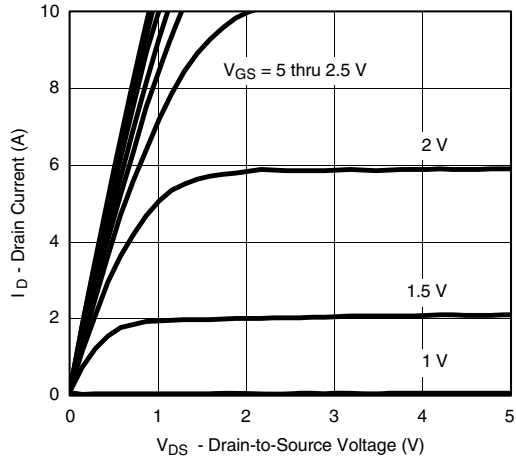
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.45		- 0.95	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 6			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -2.5\text{ V}$	- 3			
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		0.080	0.100	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -2\text{ A}$		0.110	0.150	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		6.5		S
Diode Forward Voltage	$V_{SD}$	$I_S = -0.75\text{ A}, V_{GS} = 0\text{ V}$		- 0.80	- 1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}$ $I_D \cong -2.8\text{ A}$		4.5	10	nC
Gate-Source Charge	$Q_{gs}$			0.7		
Gate-Drain Charge	$Q_{gd}$			1.1		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	2	8	16	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		375		pF
Output Capacitance	$C_{oss}$			95		
Reverse Transfer Capacitance	$C_{rss}$			65		
<b>Switching<sup>c</sup></b>						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}$ $R_g = 6\text{ }\Omega$		20	30	ns
	$t_r$			40	60	
Turn-Off Time	$t_{d(off)}$			30	45	
	$t_f$			20	30	

## Notes:

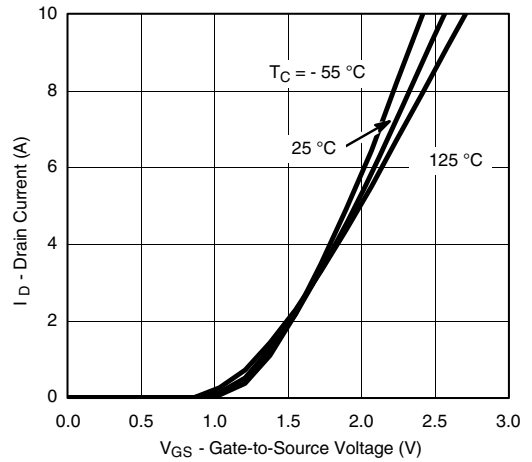
- a. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$  duty cycle  $\leq 2\%$ .  
 b. For DESIGN AID ONLY, not subject to production testing.  
 c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

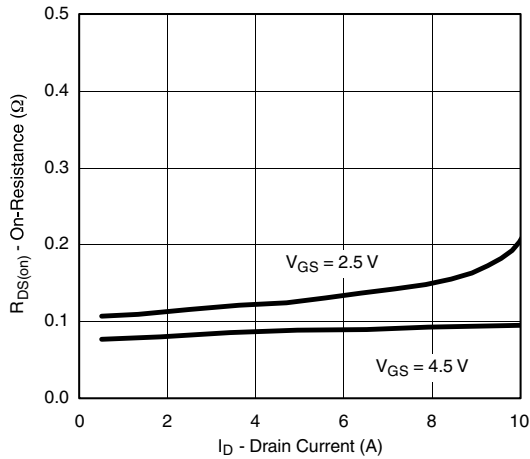
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



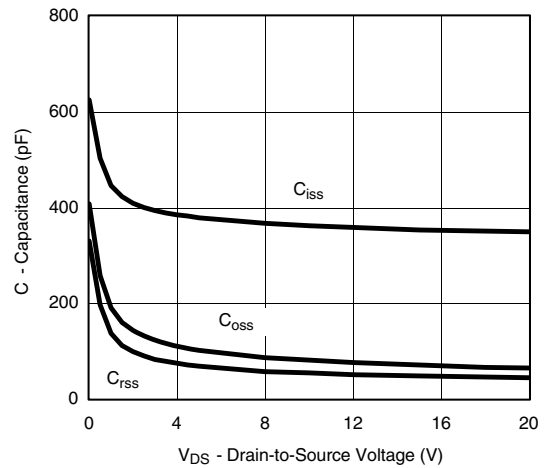
**Output Characteristics**



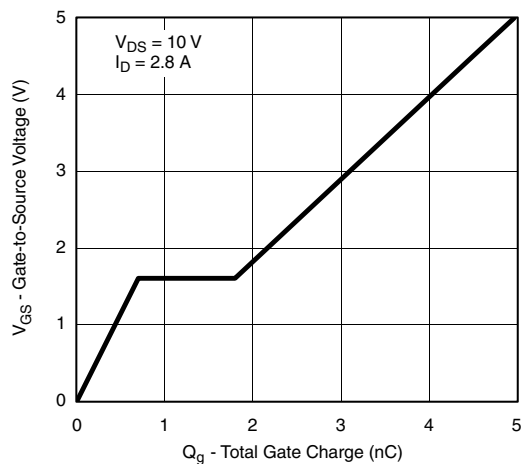
**Transfer Characteristics**



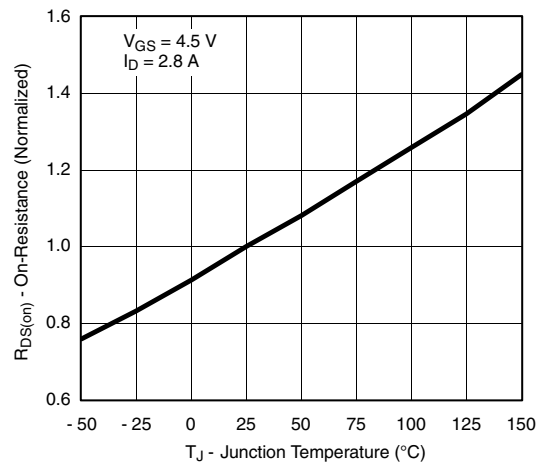
**On-Resistance vs. Drain Current**



**Capacitance**

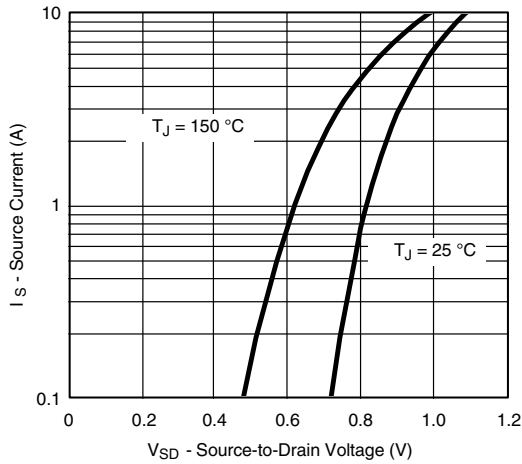


**Gate Charge**

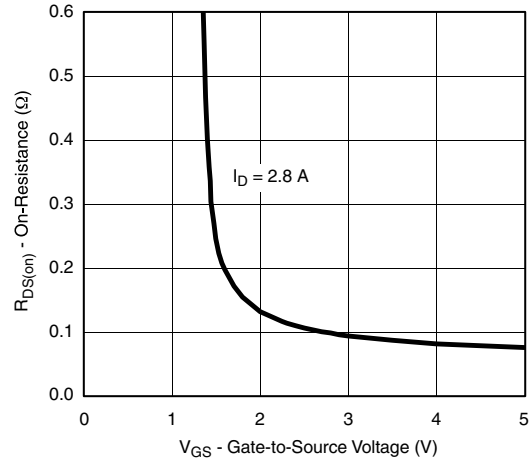


**On-Resistance vs. Junction Temperature**

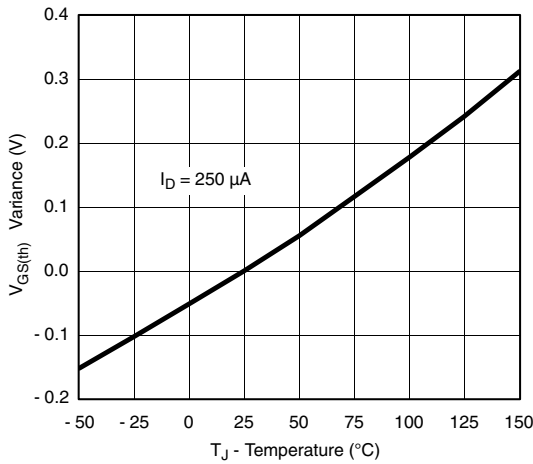
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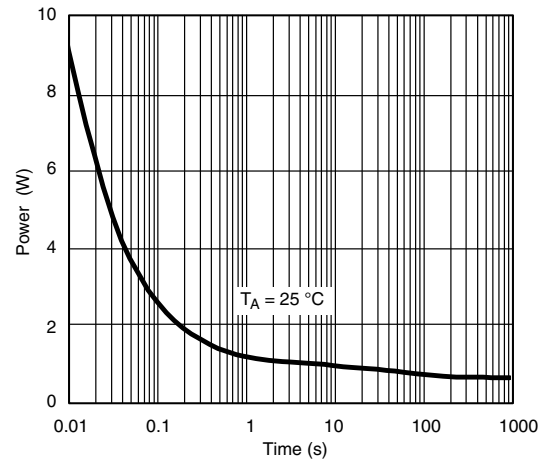
Source-Drain Diode Forward Voltage



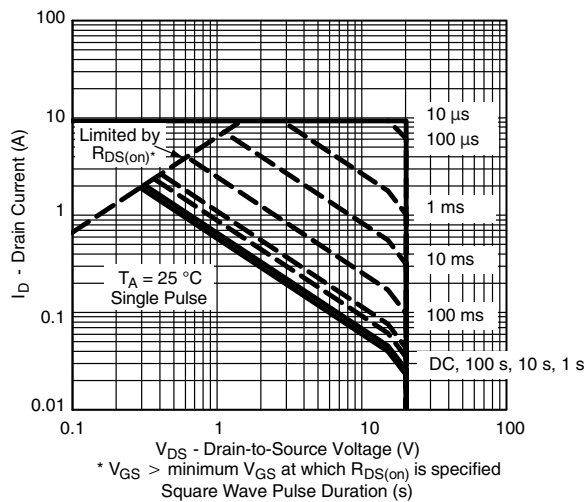
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

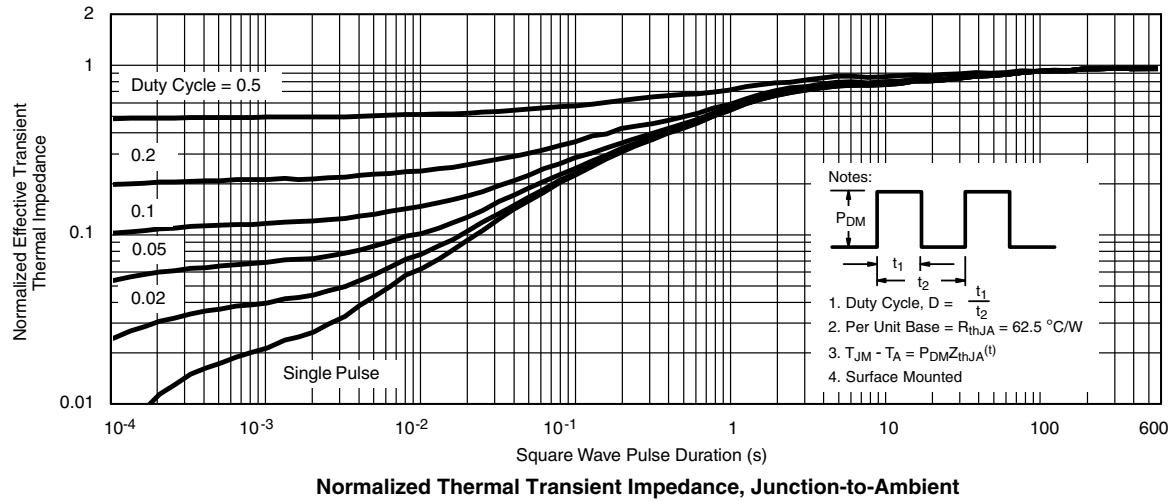


Single Pulse Power



Safe Operating Area

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



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## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
 DWG: 5479

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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